

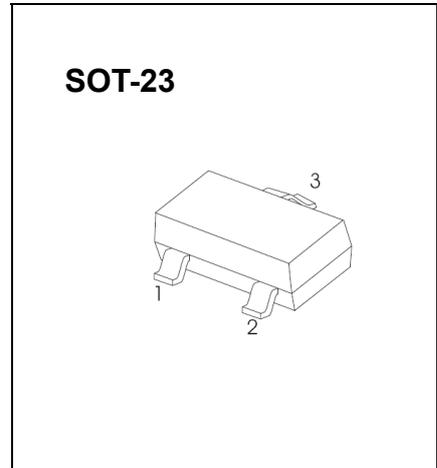


ShenzhenTaimaoTechnology Co.,Ltd.
SOT-23 Plastic-Encapsulate Diodes

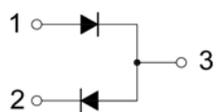
BAP64-04,05,06 Pin Diode

FEATURES

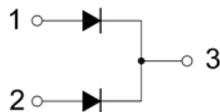
- High voltage ,current controlled
- RF resistor for RF attenuators and switches
- Low diode capacitance
- Low diode forward resistance
- Low series inductance
- For applications up to 3 GHz



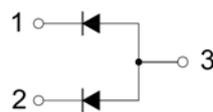
BAP64-04



BAP64-05



BAP64-06



MARKING:4K

MARKING:5K

MARKING:6K

Maximum Ratings (T_a=25°C unless otherwise specified)

Parameter	Symbol	Value	Units
Continuous reverse voltage	V _R	175	V
Continuous forward current	I _F	100	mA
Power dissipation	P _D	250	mW
Thermal resistance from junction to ambient	R _{θJA}	500	°C/W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55~150	°C

Electrical characteristic ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Forward Voltage	V_F			1.1	V	$I_F=50\text{mA}$
Reverse Current	I_{R1}			10	μA	$V_{R1}=175\text{V}$
	I_{R2}			1		$V_{R2}=20\text{V}$
Diode Capacitance	C_{d1}		0.52		pF	$V_R=0\text{V}, f=1\text{MHz}$
	C_{d2}			0.5		$V_R=1\text{V}, f=1\text{MHz}$
	C_{d3}			0.35		$V_R=20\text{V}, f=1\text{MHz}$
Diode Forward Resistance (note 1)	R_{d1}			40	Ω	$I_F=0.5\text{mA}, f=100\text{MHz}$
	R_{d2}			20		$I_F=1\text{mA}, f=100\text{MHz}$
	R_{d3}			3.8		$I_F=10\text{mA}, f=100\text{MHz}$
	R_{d4}			1.35		$I_F=100\text{mA}, f=100\text{MHz}$
Charge Carrier Life Time	τ_L		1.55		μs	When switched from $I_F=10\text{mA}$ to $I_R=6\text{mA}; R_L=100\Omega$; measured at $I_R=3\text{mA}$
Series Inductance	L_S		1.4		nH	$I_F=10\text{mA}, f=100\text{MHz}$

Note:

1. Guaranteed on AQL basis: inspection level S4, AQL 1.0.